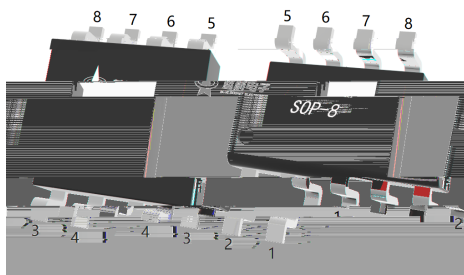
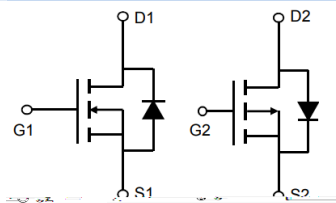


Rev.B May.-2026

Complementary Enhancement MOSFET in a SOP-8 Plastic Package.

HF Product.

Battery protection switch, Mobile device battery charging and discharging, Load switch.



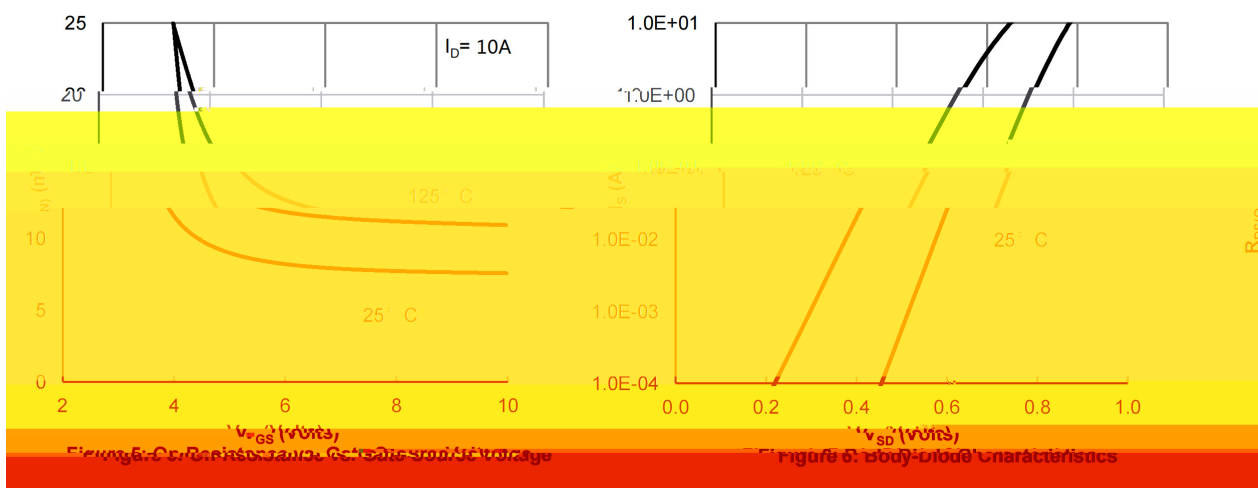
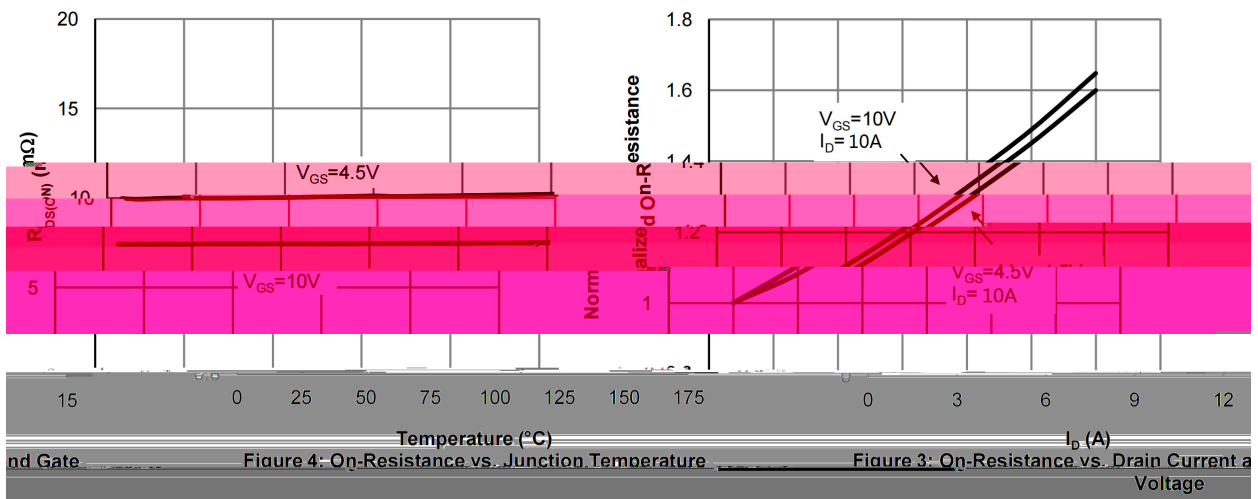
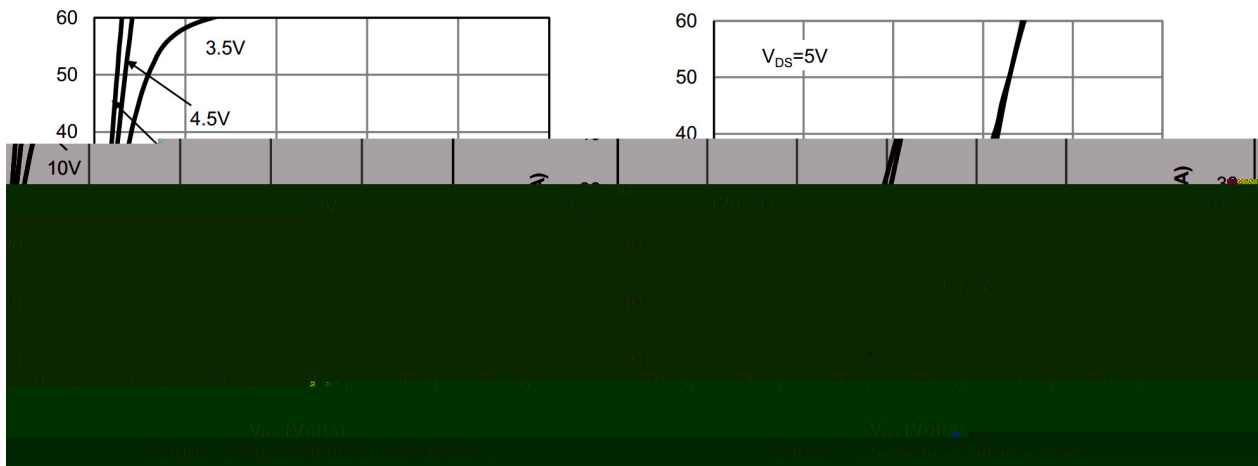
PIN1	S1	PIN 2	G1	PIN 3	S2	PIN 4	G2
PIN 5	D2	PIN 6	D2	PIN 7	D1	PIN 8	D1

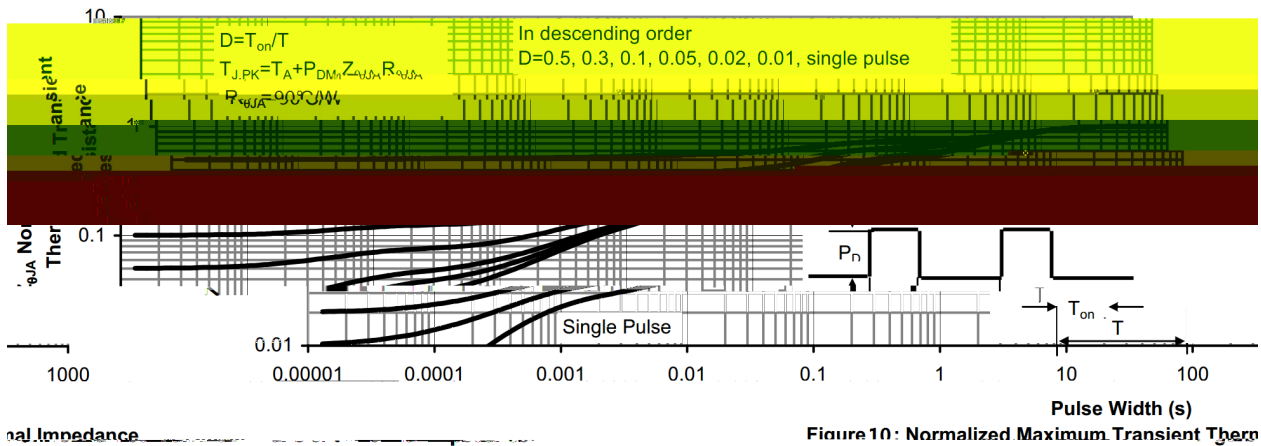
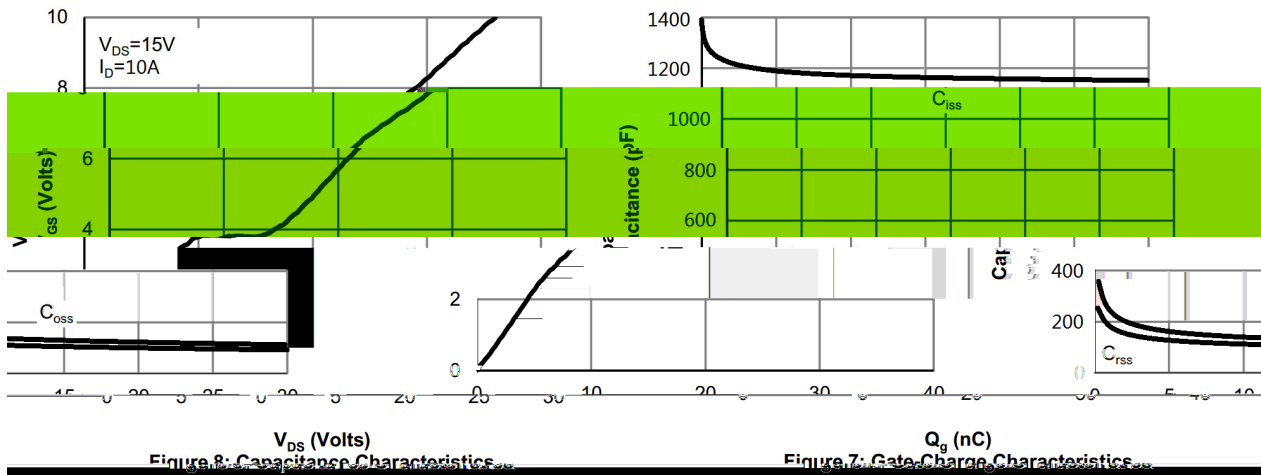
See Marking Instructions.

Parameter	Symbol	Rating		Unit
		N-channel	P-channel	
Drain-Source Voltage	V_{DS}	30	-30	V
Gate-Source Voltage	V_{GS}	± 20		V
Continuous Drain Current	I_D	15.5	-11.5	A
Pulsed Drain Current	I_{DM}	49	-37	A
Power Dissipation	P_D	3.2	3	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150		
Maximum Junction-to-Ambient	$R_{\theta JA}$	90		/W

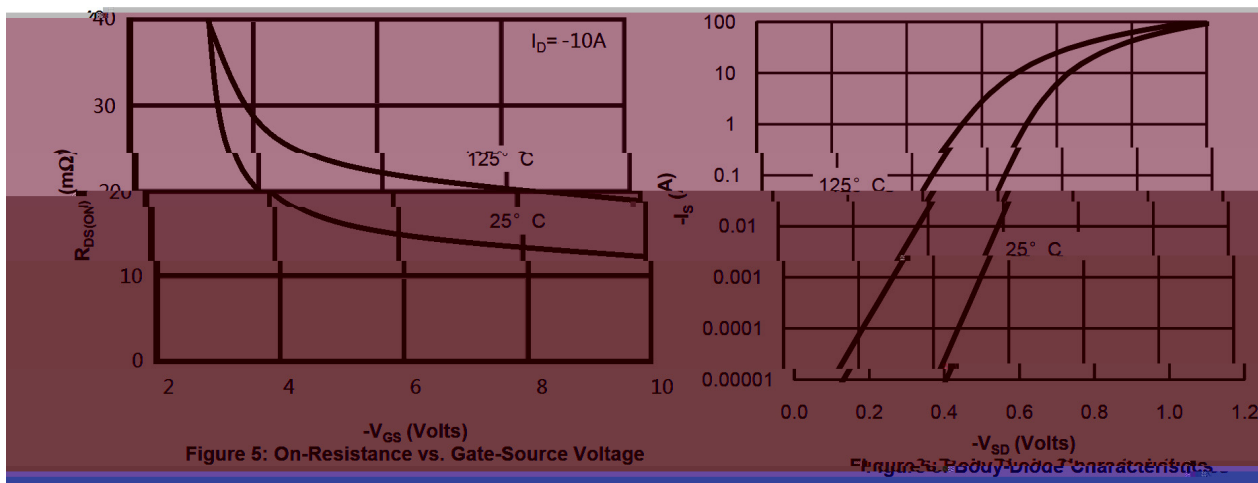
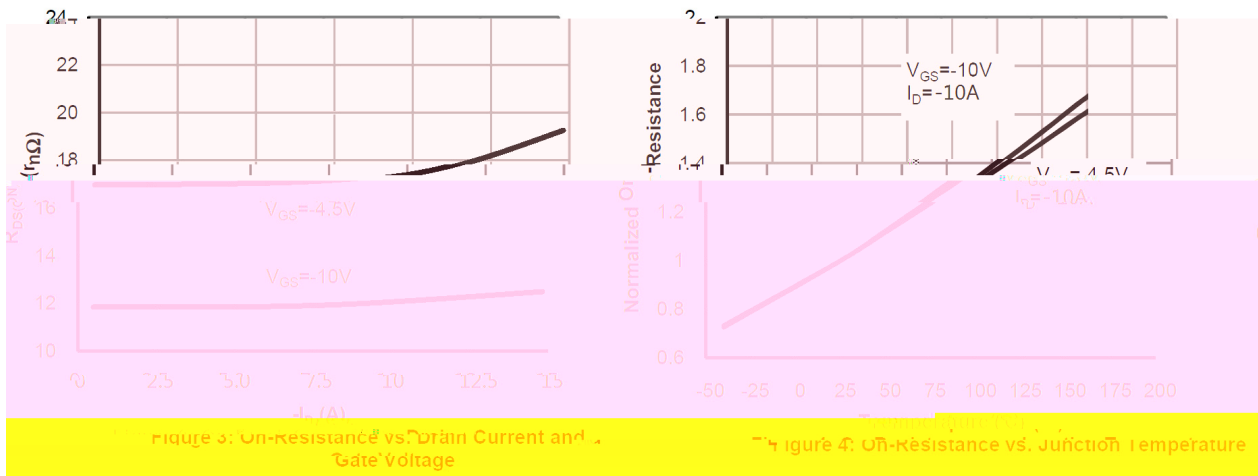
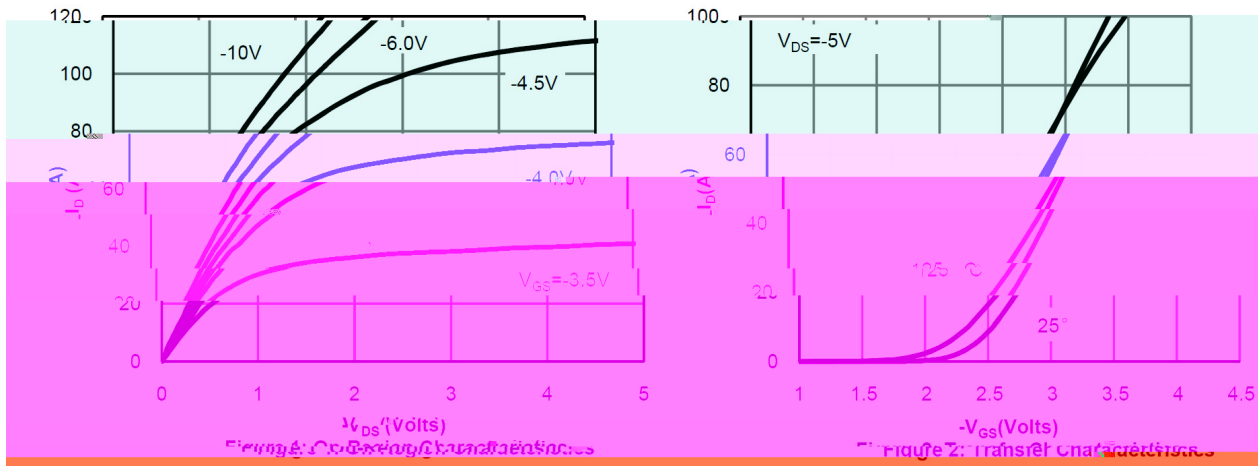
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\text{ A}$	30	35.5		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V$ $V_{GS}=0V$			1.0	A
Gate-Body leakage current	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\text{ A}$	1.0	1.8	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=10A$		7.5	8	m
		$V_{GS}=4.5V$ $I_D=10A$		11	15	m
Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=1.0A$			1.4	V
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		1170		pF
Output Capacitance	C_{oss}			110		pF
Reverse Transfer Capacitance	C_{rss}			100		pF
Gate resistance	R_g	$V_{DS}=0V$ $V_{GS}=0V$ $f=1.0MHz$		3.7		
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10V$ $V_{DS}=15V$ $I_D=10A$		40		nC
Total Gate Charge	$Q_{g(4.5V)}$			22		nC
Gate-Source Charge	Q_{gs}			11		nC
Gate-Drain Charge	Q_{gd}			5		nC
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=15\text{ V}$ $V_{GS}=10V$ $R_L=0.75$ $R_{GEN}=3$		11		ns
Turn-On Rise Time	t_r			14		ns
Turn-Off Delay Time	$t_{d(off)}$			38		ns

Turn-OffTime (L)Tj10.4958 0 0 10.5 271.2 336.5004 Tm-.e1.48001 nT=1.0A ns





Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=-250 A$	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-4030V$ $V_{GS}=0V$			-1.0	A
Gate-Body leakage current	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=-250 A$	-1.0	-1.5	-2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10V$ $I_D=-10A$		12	13	m
		$V_{GS}=-4.5V$ $I_D=-10A$		17	20	m
Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=-1.0A$			-1.4	V
Input Capacitance	C_{iss}	$V_{DS}=-25V$ $V_{GS}=0V$ $f=1.0MHz$		2100		pF
Output Capacitance	C_{oss}			1900		pF
Reverse Transfer Capacitance	C_{rss}			640		pF
Gate resistance	R_g	$V_{DS}=0V$ $V_{GS}=0V$ $f=1.0MHz$		4		
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=-10V$ $V_{DS}=-15V$ $I_D=-10A$		35		nC
Total Gate Charge	$Q_{g(4.5V)}$			17		nC
Gate-Source Charge	Q_{gs}			5.7		nC
Gate-Drain Charge	Q_{gd}			8.8		nC
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=-15 V$ $V_{GS}=-10V$ $R_L=1$ $R_{GEN}=3$		11		ns
Turn-On Rise Time	t_r			7.5		ns
Turn-Off Delay Time	$t_{d(off)}$			43.5		ns
Turn-Off Fall Time	t_f			17.5		ns



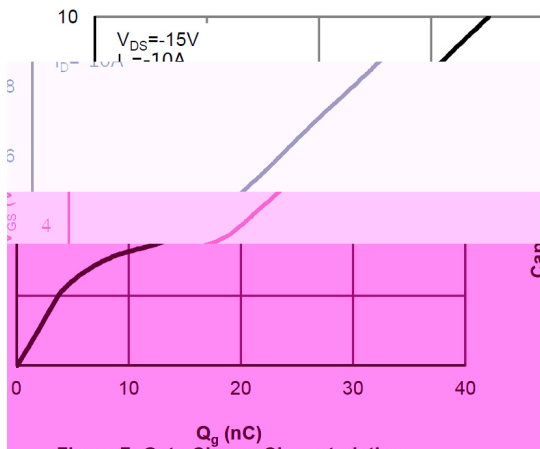


Figure 7: Gate-Charge Characteristics

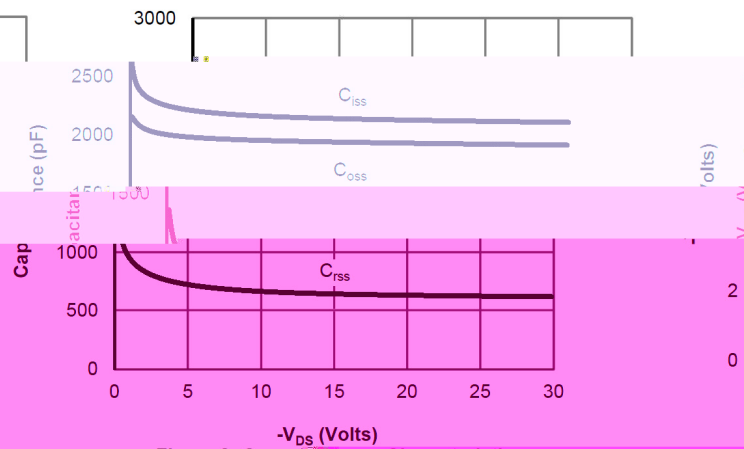


Figure 8: Capacitance Characteristics

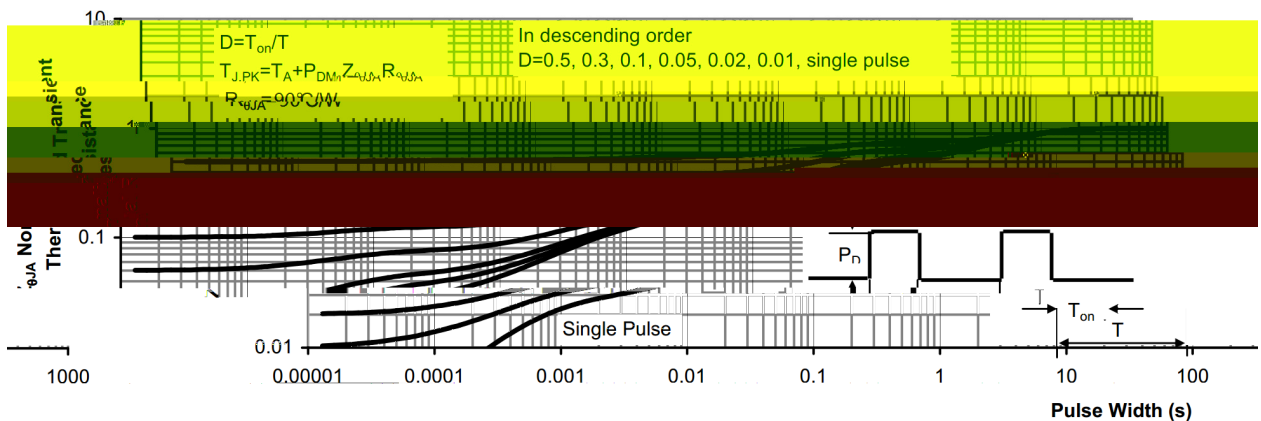
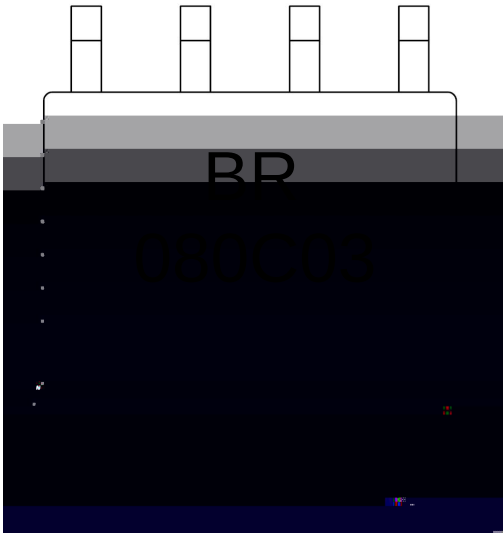


Figure 10: Normalized Maximum Transient Thermal Impedance



BR

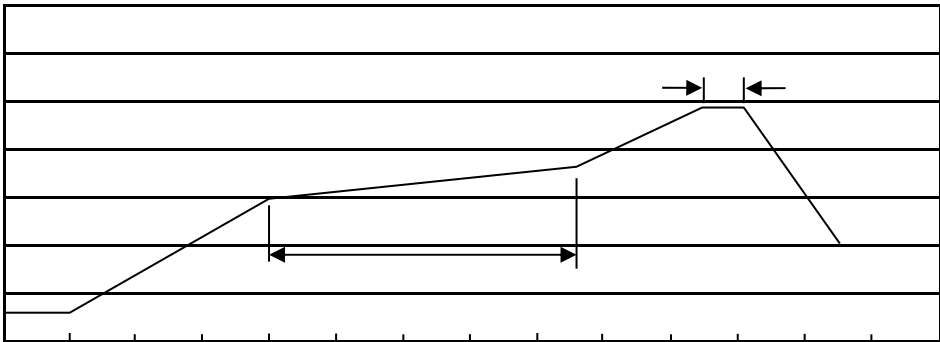
080C03

Note:

BR: Company Code

080C03: Product Type

****: Lot No. Code, code change with Lot No.



- 1

150 180

60 90sec;
- 2

245 5

5 0.5sec;
- 3

2 10 /sec.
- Note:

1.Preheating:150~180 , Time:60~90sec.

2.Peak Temp.:245 5 , Duration:5 0.5sec.

3. Cooling Speed: 2~10 /sec.

260 5

10 1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL

Package Type	Units					Dimension (unit mm ³)		
SOP/ESOP-8	4,000	2	8,000	6	48,000	13 ×12	360×360×50	380×335×366